# MC74HCT138A

# 1-of-8 Decoder/ Demultiplexer with LSTTL Compatible Inputs

## High−Performance Silicon−Gate CMOS

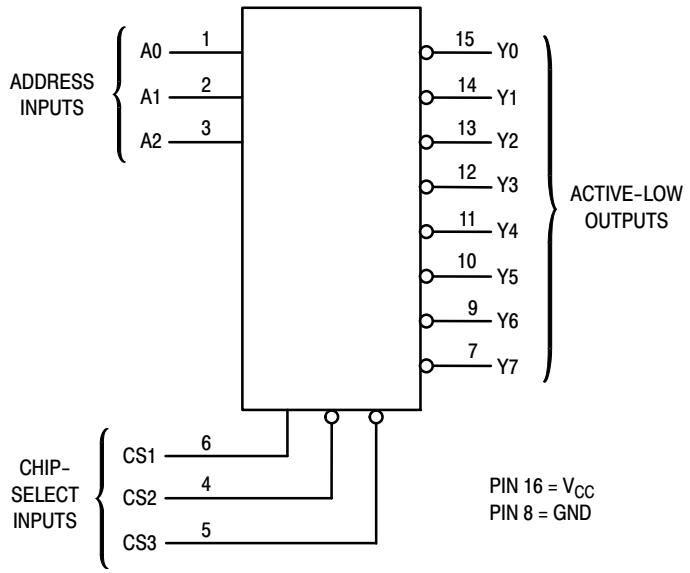
The MC74HCT138A is identical in pinout to the LS138. The HCT138A may be used as a level converter for interfacing TTL or NMOS outputs to High Speed CMOS inputs.

The HCT138A decodes a three−bit Address to one−of−eight active−lot outputs. This device features three Chip Select inputs, two active−low and one active−high to facilitate the demultiplexing, cascading, and chip−selecting functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output; one of the Chip Selects is used as a data input while the other Chip Selects are held in their active states.

### Features

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1.0 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 122 FETs or 30.5 Equivalent Gates
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

### LOGIC DIAGRAM

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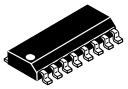
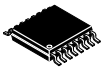
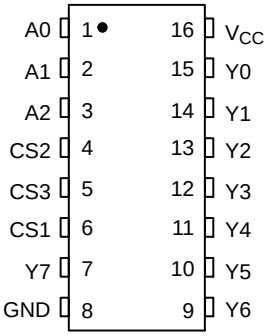


SOIC−16
D SUFFIX
CASE 751B



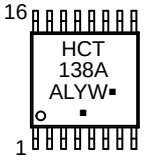
TSSOP−16
DT SUFFIX
CASE 948F

### PIN ASSIGNMENT




### MARKING DIAGRAMS


SOIC−16




TSSOP−16

| | | |
|---|---|---|
| A | = | Assembly Location |
| WL, L | = | Wafer Lot |
| YY, Y | = | Year |
| WW, W | = | Work Week |
| G or ▪ | = | Pb−Free Package |

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

| Design Criteria | Value | Units |
|---|---|---|
| Internal Gate Count* | 30.5 | ea. |
| Internal Gate Propagation Delay | 1.5 | ns |
| Internal Gate Power Dissipation | 5.0 | μW |
| Speed Power Product | .0075 | pJ |

*Equivalent to a two−input NAND gate.

## FUNCTION TABLE

| Inputs | | | | | | Outputs | | | | | | | |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| CS1 | CS2 | CS3 | A2 | A1 | A0 | Y0 | Y1 | Y2 | Y3 | Y4 | Y5 | Y6 | Y7 |
| X | X | H | X | X | X | H | H | H | H | H | H | H | H |
| X | H | X | X | X | X | H | H | H | H | H | H | H | H |
| L | X | X | X | X | X | H | H | H | H | H | H | H | H |
| H | L | L | L | L | L | L | H | H | H | H | H | H | H |
| H | L | L | L | L | H | H | L | H | H | H | H | H | H |
| H | L | L | L | H | L | H | H | L | H | H | H | H | H |
| H | L | L | L | H | H | H | H | H | L | H | H | H | H |
| H | L | L | H | L | L | H | H | H | H | L | H | H | H |
| H | L | L | H | L | H | H | H | H | H | H | L | H | H |
| H | L | L | H | H | L | H | H | H | H | H | H | L | H |
| H | L | L | H | H | H | H | H | H | H | H | H | H | L |

H = high level (steady state)
L = low level (steady state)
X = don't care

## MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|---|---|---|---|
| $V_{CC}$ | DC Supply Voltage (Referenced to GND) | –0.5 to +7.0 | V |
| $V_{in}$ | DC Input Voltage (Referenced to GND) | –0.5 to $V_{CC}$ + 0.5 | V |
| $V_{out}$ | DC Output Voltage (Referenced to GND) | –0.5 to $V_{CC}$ + 0.5 | V |
| $I_{in}$ | DC Input Current, per Pin | ±20 | mA |
| $I_{out}$ | DC Output Current, per Pin | ±25 | mA |
| $I_{CC}$ | DC Supply Current, $V_{CC}$ and GND Pins | ±50 | mA |
| $P_D$ | Power Dissipation in Still Air SOIC Package†<br>TSSOP Package† | 500<br>450 | mW |
| $T_{stg}$ | Storage Temperature | –65 to +150 | °C |
| $T_L$ | Lead Temperature, 1 mm from Case for 10 Seconds (TSSOP or SOIC Package) | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
†Derating: SOIC Package: –7 mW/°C from 65° to 125°C
TSSOP Package: −6.1 mW/°C from 65° to 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, $V_{in}$ and $V_{out}$ should be constrained to the range GND ≤ ($V_{in}$ or $V_{out}$) ≤ $V_{CC}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $V_{CC}$). Unused outputs must be left open.

## RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
|---|---|---|---|---|
| $V_{CC}$ | DC Supply Voltage (Referenced to GND) | 2.0 | 6.0 | V |
| $V_{in}$, $V_{out}$ | DC Input Voltage, Output Voltage (Referenced to GND) | 0 | $V_{CC}$ | V |
| $T_A$ | Operating Temperature, All Package Types | –55 | +125 | °C |
| $t_r$, $t_f$ | Input Rise and Fall Time (Figure 1) | 0 | 500 | ns |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

| Symbol | Parameter | Test Conditions | $V_{CC}$ V | Guaranteed Limit | | | Unit |
|---|---|---|---|---|---|---|---|
| | | | | –55 to 25°C | ≤ 85°C | ≤ 125°C | |
| $V_{IH}$ | Minimum High−Level Input Voltage | $V_{out}$ = 0.1 V or $V_{CC}$ – 0.1 V<br>$\|I_{out}\| \le 20$ μA | 4.5<br>5.5 | 2.0<br>2.0 | 2.0<br>2.0 | 2.0<br>2.0 | V |
| $V_{IL}$ | Maximum Low−Level Input Voltage | $V_{out}$ = 0.1 V or $V_{CC}$ – 0.1 V<br>$\|I_{out}\| \le 20$ μA | 4.5<br>5.5 | 0.8<br>0.8 | 0.8<br>0.8 | 0.8<br>0.8 | V |
| $V_{OH}$ | Minimum High−Level Output Voltage | $V_{in}$ = $V_{IH}$ or $V_{IL}$<br>$\|I_{out}\| \le 20$ μA | 4.5<br>5.5 | 4.4<br>5.4 | 4.4<br>5.4 | 4.4<br>5.4 | V |
| | | $V_{in}$ = $V_{IH}$ or $V_{IL}$<br>$\|I_{out}\| \le 4.0$ mA | 4.5 | 3.98 | 3.84 | 3.7 | |
| $V_{OL}$ | Maximum Low−Level Output Voltage | $V_{in}$ = $V_{IH}$ or $V_{IL}$<br>$\|I_{out}\| \le 20$ μA | 4.5<br>5.5 | 0.1<br>0.1 | 0.1<br>0.1 | 0.1<br>0.1 | V |
| | | $V_{in}$ = $V_{IH}$ or $V_{IL}$<br>$\|I_{out}\| \le 4.0$ mA | 4.5 | 0.26 | 0.33 | 0.4 | |
| $I_{in}$ | Maximum Input Leakage Current | $V_{in}$ = $V_{CC}$ or GND | 6.0 | ±0.1 | ±1.0 | ±1.0 | μA |
| $I_{CC}$ | Maximum Quiescent Supply Current (per Package) | $V_{in}$ = $V_{CC}$ or GND<br>$I_{out}$ = 0 μA | 5.5 | 4.0 | 40 | 160 | μA |
| | | $V_{in}$ = 2.4 V, Any One Input<br>$V_{in}$ = $V_{CC}$ or GND, Other Inputs<br>$I_{out}$ = 0 μA | | ≥ –55°C | 25°C to 125°C | | |
| $\Delta I_{CC}$ | Additional Quiescent Supply Current | | 5.5 | 2.9 | 2.4 | | mA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

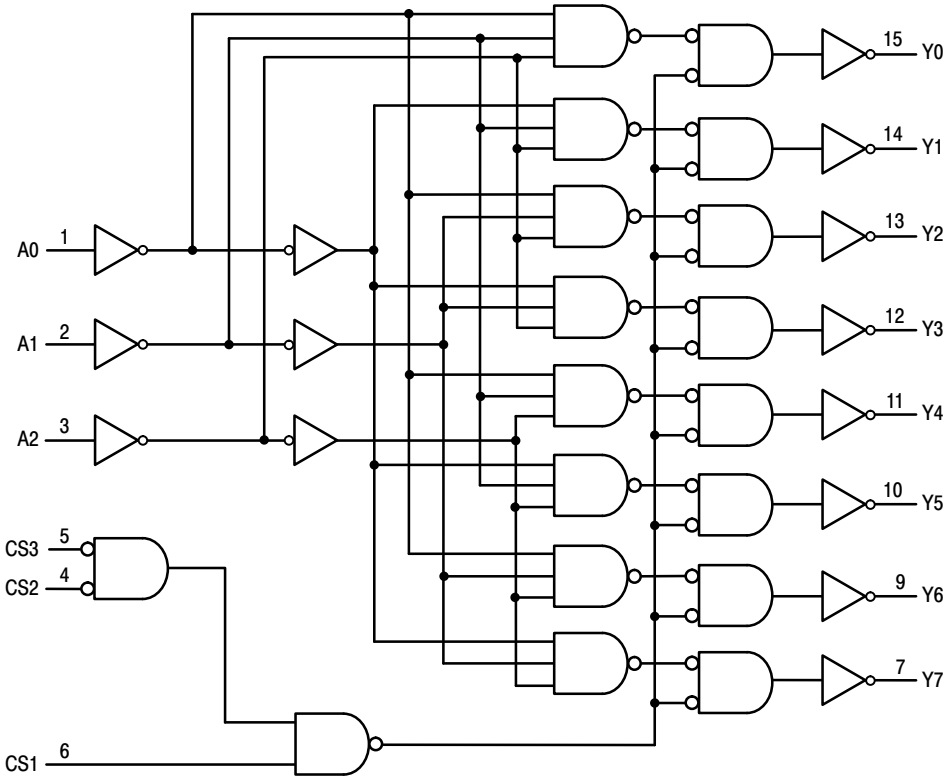
## AC ELECTRICAL CHARACTERISTICS ($V_{CC}$ = 5.0 V ±10%, $C_L$ = 50 pF, Input $t_r$ = $t_f$ = 6.0 ns)

| Symbol | Parameter | Guaranteed Limit | | | Unit |
|---|---|---|---|---|---|
| | | –55 to 25°C | ≤ 85°C | ≤ 125°C | |
| $t_{PLH}$, $t_{PHL}$ | Maximum Propagation Delay, Input A to Output Y (Figures 1 and 4) | 30 | 38 | 45 | ns |
| $t_{PLH}$, $t_{PHL}$ | Maximum Propagation Delay, CS1 to Output Y (Figures 2 and 4) | 27 | 34 | 41 | ns |
| $t_{PLH}$, $t_{PHL}$ | Maximum Output Transition Time, CS2 or CS3 to Output Y (Figures 3 and 4) | 30 | 38 | 45 | ns |
| $t_{TLH}$, $t_{THL}$ | Maximum Output Transition Time, Any Output (Figures 2 and 4) | 15 | 19 | 22 | ns |
| $t_r$, $t_f$ | Maximum Input Rise and Fall Time | 500 | 500 | 500 | ns |
| $C_{in}$ | Maximum Input Capacitance | 10 | 10 | 10 | pF |

| | | Typical @ 25°C, $V_{CC}$ = 5.0 V | |
|---|---|---|---|
| $C_{PD}$ | Power Dissipation Capacitance (Per Enabled Output)* | 51 | pF |

* Used to determine the no−load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

## EXPANDED LOGIC DIAGRAM




## SWITCHING WAVEFORMS

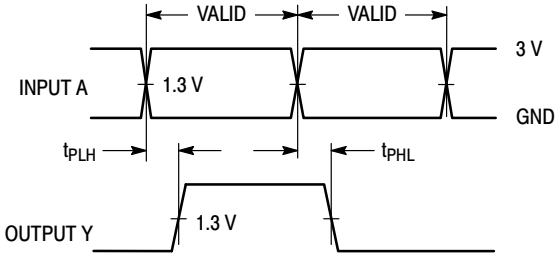



**Figure 1.**

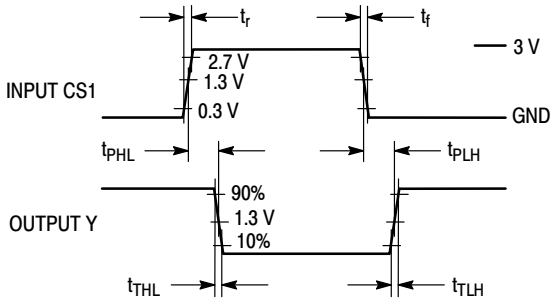



**Figure 2.**

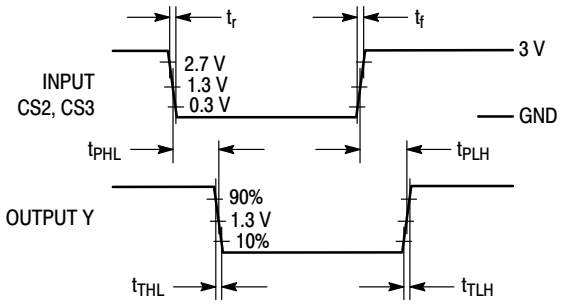
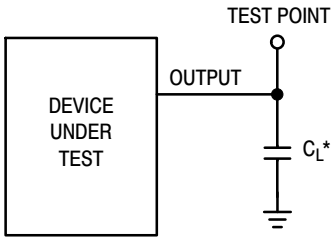



**Figure 3.**

## TEST CIRCUIT




*Includes all probe and jig capacitance

**Figure 4.**

## ORDERING INFORMATION

| Device | Package | Shipping† |
|---|---|---|
| MC74HCT138ADG | SOIC−16<br>(Pb−Free) | 48 Units / Rail |
| MC74HCT138ADR2G | SOIC−16<br>(Pb−Free) | 2500 Units / Tape & Reel |
| MC74HCT138ADTR2G | TSSOP−16<br>(Pb−Free) | 2500 Units / Tape & Reel |

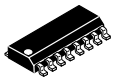
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MECHANICAL CASE OUTLINE
## PACKAGE DIMENSIONS

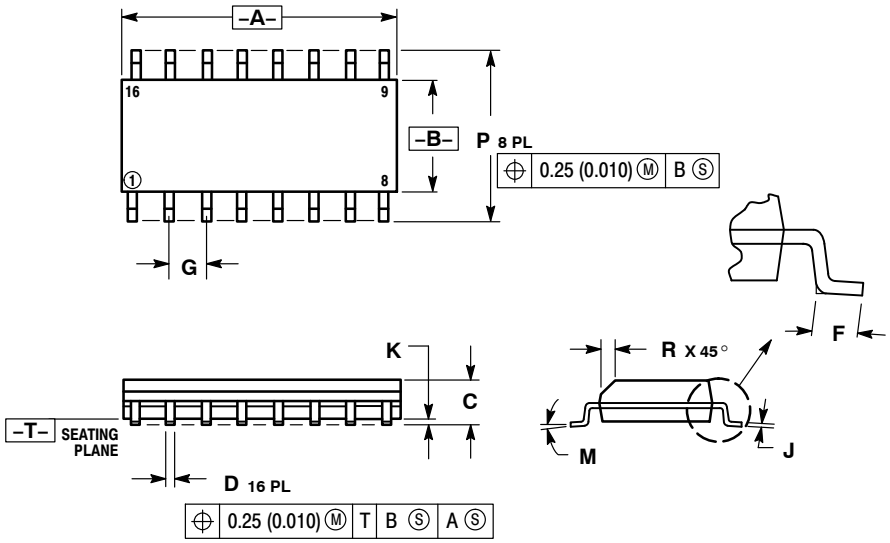
ON Semiconductor®

**SOIC−16**
CASE 751B−05
ISSUE K

DATE 29 DEC 2006



SCALE 1:1




NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

| | MILLIMETERS | | INCHES | |
|---|---|---|---|---|
| DIM | MIN | MAX | MIN | MAX |
| A | 9.80 | 10.00 | 0.386 | 0.393 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.054 | 0.068 |
| D | 0.35 | 0.49 | 0.014 | 0.019 |
| F | 0.40 | 1.25 | 0.016 | 0.049 |
| G | 1.27 BSC | | 0.050 BSC | |
| J | 0.19 | 0.25 | 0.008 | 0.009 |
| K | 0.10 | 0.25 | 0.004 | 0.009 |
| M | 0° | 7° | 0° | 7° |
| P | 5.80 | 6.20 | 0.229 | 0.244 |
| R | 0.25 | 0.50 | 0.010 | 0.019 |

STYLE 1:
| | |
|---|---|
| PIN 1. | COLLECTOR |
| 2. | BASE |
| 3. | EMITTER |
| 4. | NO CONNECTION |
| 5. | EMITTER |
| 6. | BASE |
| 7. | COLLECTOR |
| 8. | COLLECTOR |
| 9. | BASE |
| 10. | EMITTER |
| 11. | NO CONNECTION |
| 12. | EMITTER |
| 13. | BASE |
| 14. | COLLECTOR |
| 15. | EMITTER |
| 16. | COLLECTOR |

STYLE 2:
| | |
|---|---|
| PIN 1. | CATHODE |
| 2. | ANODE |
| 3. | NO CONNECTION |
| 4. | CATHODE |
| 5. | CATHODE |
| 6. | NO CONNECTION |
| 7. | ANODE |
| 8. | CATHODE |
| 9. | CATHODE |
| 10. | ANODE |
| 11. | NO CONNECTION |
| 12. | CATHODE |
| 13. | CATHODE |
| 14. | NO CONNECTION |
| 15. | ANODE |
| 16. | CATHODE |

STYLE 3:
| | |
|---|---|
| PIN 1. | COLLECTOR, DYE #1 |
| 2. | BASE, #1 |
| 3. | EMITTER, #1 |
| 4. | COLLECTOR, #1 |
| 5. | COLLECTOR, #2 |
| 6. | BASE, #2 |
| 7. | EMITTER, #2 |
| 8. | COLLECTOR, #2 |
| 9. | COLLECTOR, #3 |
| 10. | BASE, #3 |
| 11. | EMITTER, #3 |
| 12. | COLLECTOR, #3 |
| 13. | COLLECTOR, #4 |
| 14. | BASE, #4 |
| 15. | EMITTER, #4 |
| 16. | COLLECTOR, #4 |

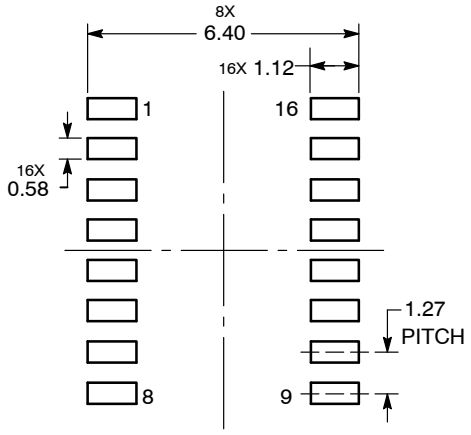
STYLE 4:
| | |
|---|---|
| PIN 1. | COLLECTOR, DYE #1 |
| 2. | COLLECTOR, #1 |
| 3. | COLLECTOR, #2 |
| 4. | COLLECTOR, #2 |
| 5. | COLLECTOR, #3 |
| 6. | COLLECTOR, #3 |
| 7. | COLLECTOR, #4 |
| 8. | COLLECTOR, #4 |
| 9. | BASE, #4 |
| 10. | EMITTER, #4 |
| 11. | BASE, #3 |
| 12. | EMITTER, #3 |
| 13. | BASE, #2 |
| 14. | EMITTER, #2 |
| 15. | BASE, #1 |
| 16. | EMITTER, #1 |

STYLE 5:
| | |
|---|---|
| PIN 1. | DRAIN, DYE #1 |
| 2. | DRAIN, #1 |
| 3. | DRAIN, #2 |
| 4. | DRAIN, #2 |
| 5. | DRAIN, #3 |
| 6. | DRAIN, #3 |
| 7. | DRAIN, #4 |
| 8. | DRAIN, #4 |
| 9. | GATE, #4 |
| 10. | SOURCE, #4 |
| 11. | GATE, #3 |
| 12. | SOURCE, #3 |
| 13. | GATE, #2 |
| 14. | SOURCE, #2 |
| 15. | GATE, #1 |
| 16. | SOURCE, #1 |

STYLE 6:
| | |
|---|---|
| PIN 1. | CATHODE |
| 2. | CATHODE |
| 3. | CATHODE |
| 4. | CATHODE |
| 5. | CATHODE |
| 6. | CATHODE |
| 7. | CATHODE |
| 8. | CATHODE |
| 9. | ANODE |
| 10. | ANODE |
| 11. | ANODE |
| 12. | ANODE |
| 13. | ANODE |
| 14. | ANODE |
| 15. | ANODE |
| 16. | ANODE |

STYLE 7:
| | |
|---|---|
| PIN 1. | SOURCE N-CH |
| 2. | COMMON DRAIN (OUTPUT) |
| 3. | COMMON DRAIN (OUTPUT) |
| 4. | GATE P-CH |
| 5. | COMMON DRAIN (OUTPUT) |
| 6. | COMMON DRAIN (OUTPUT) |
| 7. | COMMON DRAIN (OUTPUT) |
| 8. | SOURCE P-CH |
| 9. | SOURCE P-CH |
| 10. | COMMON DRAIN (OUTPUT) |
| 11. | COMMON DRAIN (OUTPUT) |
| 12. | COMMON DRAIN (OUTPUT) |
| 13. | GATE N-CH |
| 14. | COMMON DRAIN (OUTPUT) |
| 15. | COMMON DRAIN (OUTPUT) |
| 16. | SOURCE N-CH |

### SOLDERING FOOTPRINT

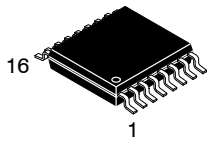



DIMENSIONS: MILLIMETERS

| DOCUMENT NUMBER: | 98ASB42566B | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
|---|---|---|
| DESCRIPTION: | SOIC−16 | PAGE 1 OF 1 |

# MECHANICAL CASE OUTLINE
## PACKAGE DIMENSIONS

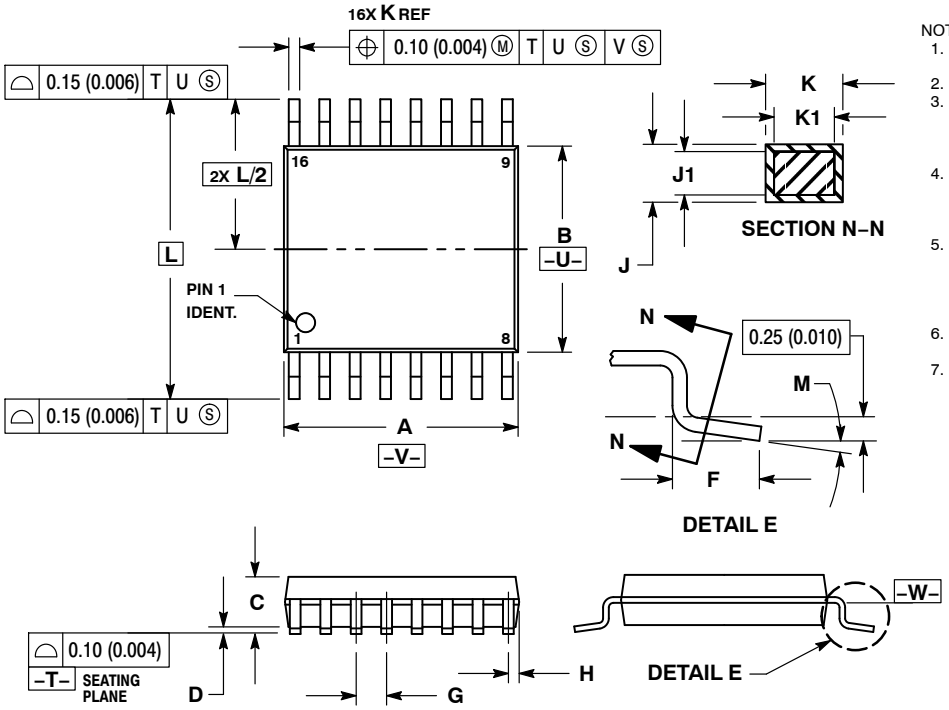
ON Semiconductor®




SCALE 2:1

**TSSOP−16**
CASE 948F−01
ISSUE B

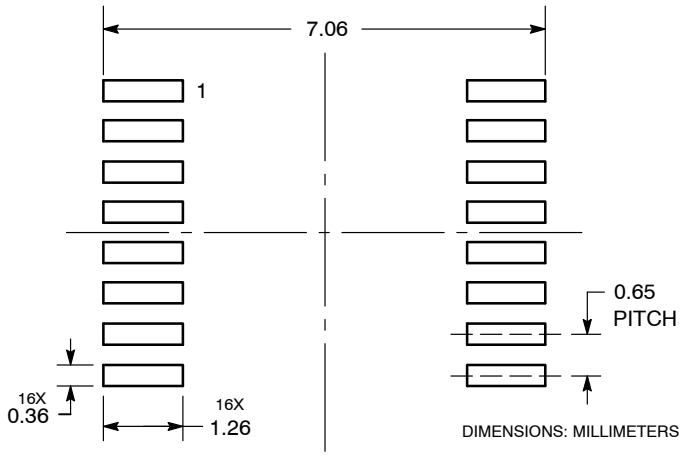
DATE 19 OCT 2006




NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

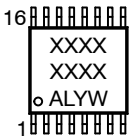
| | MILLIMETERS | | INCHES | |
|---|---|---|---|---|
| DIM | MIN | MAX | MIN | MAX |
| A | 4.90 | 5.10 | 0.193 | 0.200 |
| B | 4.30 | 4.50 | 0.169 | 0.177 |
| C | −−− | 1.20 | −−− | 0.047 |
| D | 0.05 | 0.15 | 0.002 | 0.006 |
| F | 0.50 | 0.75 | 0.020 | 0.030 |
| G | 0.65 BSC | | 0.026 BSC | |
| H | 0.18 | 0.28 | 0.007 | 0.011 |
| J | 0.09 | 0.20 | 0.004 | 0.008 |
| J1 | 0.09 | 0.16 | 0.004 | 0.006 |
| K | 0.19 | 0.30 | 0.007 | 0.012 |
| K1 | 0.19 | 0.25 | 0.007 | 0.010 |
| L | 6.40 BSC | | 0.252 BSC | |
| M | 0 ° | 8 ° | 0 ° | 8 ° |

### SOLDERING FOOTPRINT




DIMENSIONS: MILLIMETERS

### GENERIC MARKING DIAGRAM*




| | |
|---|---|
| XXXX | = Specific Device Code |
| A | = Assembly Location |
| L | = Wafer Lot |
| Y | = Year |
| W | = Work Week |
| G or ▪ | = Pb−Free Package |

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

| | | |
|---|---|---|
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